



SKiM[®] 5

IGBT Modules

SKiM 500GD128DM

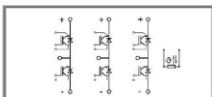
Preliminary Data

Features

- Homogeneous Si
- SPT = Soft Punch Through Technology
- V_{CEsat} with positive temperature coefficient
- High Short circuit capability, self limiting to $6 \times I_C$
- Isolated by AlN DCB (Direct Copper Bonded) ceramic plate
- Pressure contact technology for thermal contacts
- Spring contact system to attach driver PCB to the control terminals
- Integrated temperature sensor

Typical Applications

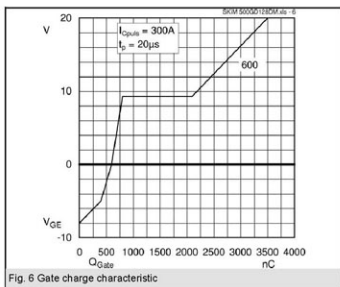
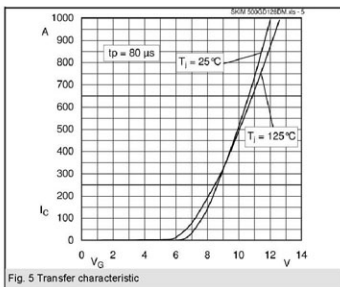
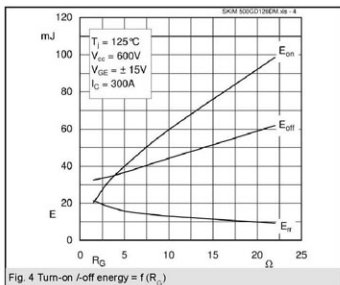
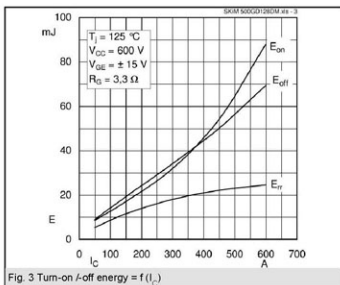
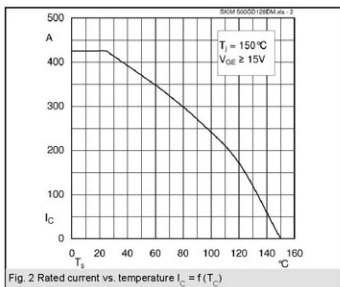
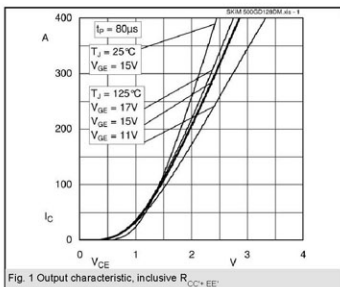
- AC inverter drives
- Uninterruptable Power supplies

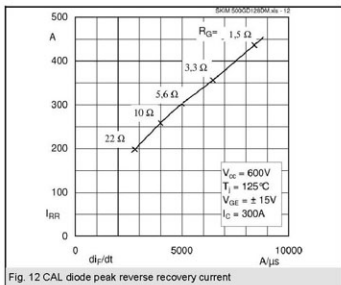
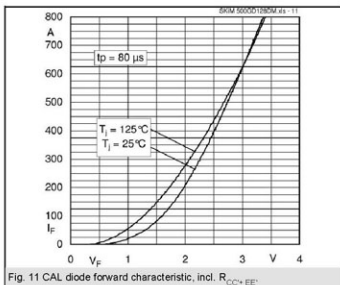
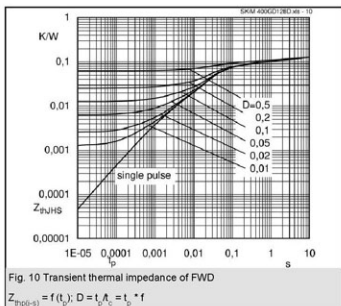
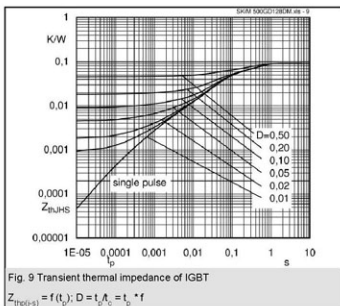
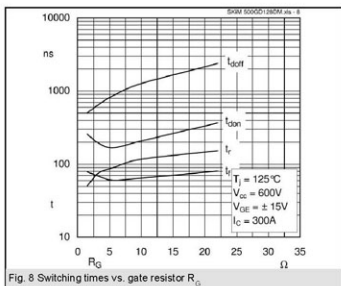
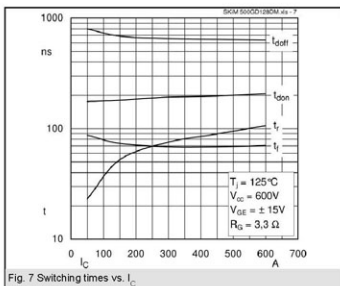


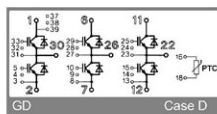
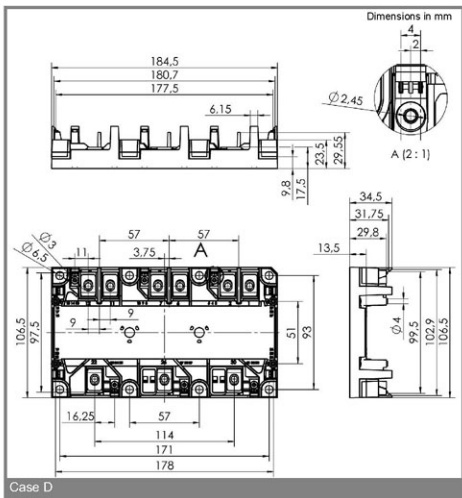
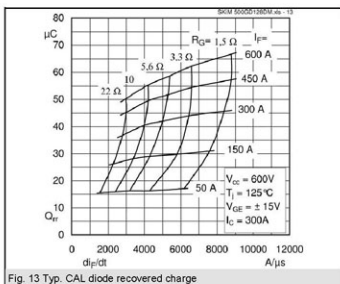
GD

Absolute Maximum Ratings		$T_c = 25^\circ\text{C}$, unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}		1200		V
I_C	$T_s = 25 (70)^\circ\text{C}$	425 (325)		A
I_{CRM}	$t_p = 1 \text{ ms}$	600		A
V_{GES}		± 20		V
T_j (T_{stg})		-40 ... +150 (125)		$^\circ\text{C}$
T_{cop}	max. case operating temperature	125		$^\circ\text{C}$
V_{bccl}	AC, 1 min.	2500		V
Inverse diode				
I_F	$T_s = 25 (70)^\circ\text{C}$	450 (340)		A
I_{FRM}	$t_p = 1 \text{ ms}$	600		A
I_{FSM}	$t_p = 10 \text{ ms}$; \sin ; $T_j = 150^\circ\text{C}$	3300		A

Characteristics		$T_{case} = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$; $I_C = 9 \text{ mA}$	4,45	5,5	6,55	V
I_{CES}	$V_{GE} = 0$; $V_{CE} = V_{CES}$; $T_j = 25^\circ\text{C}$			0,3	mA
V_{CEO}	$T_j = 25 (125)^\circ\text{C}$		1 (0,9)	1,15 (1,05)	V
r_{CE}	$T_j = 25 (125)^\circ\text{C}$		3,3 (4,7)	4 (5)	m Ω
V_{CEsat}	$I_{Cnom} = 300 \text{ A}$; $V_{GE} = 15 \text{ V}$; $T_j = 25 (125)^\circ\text{C}$ on chip level		2 (2,3)	2,35 (2,55)	V
C_{iss}	$V_{GE} = 0$; $V_{CE} = 25 \text{ V}$; $f = 1 \text{ MHz}$		27		nF
C_{oss}	$V_{GE} = 0$; $V_{CE} = 25 \text{ V}$; $f = 1 \text{ MHz}$		6,5		nF
C_{res}	$V_{GE} = 0$; $V_{CE} = 25 \text{ V}$; $f = 1 \text{ MHz}$		5,4		nF
L_{CE}				20	nH
$R_{DCE+EE'}$	resistance, terminal-chip $T_c = 25 (125)^\circ\text{C}$		0,9 (1,1)		m Ω
$t_{v(on)}$	$V_{CC} = 600 \text{ V}$		190		ns
t_r	$I_{Cnom} = 300 \text{ A}$		75		ns
$t_{v(off)}$	$R_{Con} = R_{Coff} = 3,3 \Omega$		650		ns
t_f	$T_j = 125^\circ\text{C}$		70		ns
$E_{on} (E_{off})$	$V_{GE} = 15 \text{ V}$		32 (34)		mJ
$E_{on} (E_{off})$	with SKHI 65; $T_j = 125^\circ\text{C}$; $V_{CC} = 600 \text{ V}$; $I_C = 300 \text{ A}$		35 (44)		mJ
Inverse diode					
$V_F = V_{EC}$	$I_{Fnom} = 300 \text{ A}$; $V_{GE} = 0 \text{ V}$; $T_j = 25 (125)^\circ\text{C}$		2,3 (2,1)	2,6	V
V_{TO}	$T_j = 125^\circ\text{C}$		1,1		V
r_T	$T_j = 125^\circ\text{C}$		3,3		m Ω
I_{FRM}	$I_F = 300 \text{ A}$; $T_j = 125^\circ\text{C}$		360		A
C_{rr}	$V_{GE} = 0 \text{ V}$ $di/dt = 6300 \text{ A}/\mu\text{s}$		45		μC
E_{rr}	$R_{Con} = R_{Coff} = 3,3 \Omega$		18		mJ
Thermal characteristics					
$R_{th(j-s)}$	per IGBT			0,09	K/W
$R_{th(j-a)}$	per FWD			0,125	K/W
Temperature Sensor					
R_{TS}	$T = 25 (100)^\circ\text{C}$		1 (1,67)		k Ω
tolerance	$T = 25 (100)^\circ\text{C}$		3 (2)		%
Mechanical data					
M_1	to heatsink (M5)	2		3	Nm
M_2	for terminals (M6)	4		5	Nm
w				460	g







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.